FORM PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	Atty. Docket No. 80236DPCW Customer No. 01333	Serial No. To Be Assigned
If AFTER the later date of the first Office Action or 3 months from filing, use only with Rule 97(E) Certificate or Fee	Applicant: Ramanathan Srinivasan, et al	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	Filing Date Herewith	Group To Be Assigned

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Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	5,759,917	02Jun1998	Grover et al.	438	690	
	6,299,659 B1	09Oct2001	Kido et al.	51	309	
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	6,436,835	20Aug2002	Kido et al.	438	693	

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	WO99/43761	01Sep1999	PCT **(See EP1061111A1 for english equivalent)**			X	
	EP 1 061 111 A1	20Dec2000	EPO **(Eng. Eqv. WO99/43761)**			X	
	0 786 504 A2	30Jul1997	EP	C09G	1/02	X	
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	Application of Ceria-Based High Selectivity Slurry to STI CMP for Sub 0.18 μm CMOS Technologies; by Ki-Sik Choi, Sang-Ick Lee, Chang-Il Kim, Chul-Woo Nam, Sam-Dong Kim, and Chung-Tae Kim; CMP-MIC Conference, February 11-12, 1999, pages 307-313.
	A Production-Proven Shallow Trench Isolation (STI) Solution Using Novel CMP Concepts; by Raymond R. Jin, Jeffery David, Bob Abbassi, Tom Osterheld, and Fritz Redeker; CMP-MIC Conference, February 11-12, 1999, pages 314-321.
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EXAMINER	DATE CONSIDERED 9/8/05

*EXAMINER: *Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.*